2-Input NOR Gate / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

The MC74VHC1GT02 is a single gate 2–input NOR fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0V CMOS logic to 5.0V CMOS Logic or from 1.8V CMOS logic to 3.0V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT02 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1GT02 to be used to interface 5V circuits to 3V circuits. The output structures also provide protection when $V_{\mbox{\footnotesize{CC}}}=0V$. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: tpD = 4.7ns (Typ) at VCC = 5V
- Low Power Dissipation: $I_{CC} = 2\mu A$ (Max) at $T_A = 25$ °C
- TTL-Compatible Inputs: V_{IL} = 0.8V; V_{IH} = 2.0V
- CMOS–Compatible Outputs: $V_{OH} > 0.8V_{CC}$; $V_{OL} < 0.1V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V

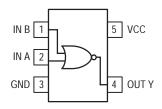
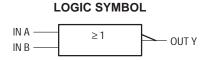


Figure 1. 5-Lead SOT-353 Pinout (Top View)





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SC-88A / SOT-353 DF SUFFIX CASE 419A

MARKING DIAGRAM



d = Date Code

	PIN ASSIGNMENT								
1	IN B								
2	IN A								
3	GND								
4	OUT Y								
5	VCC								

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

Inp	uts	Output
Α	В	Υ
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	VCC	-0.5 to +7.0	V
DC Input Voltage	VIN	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	Vout	−0.5 to 7.0 −0.5 to V _{CC} + 0.5	V
Input Diode Current	lık	-20	mA
Output Diode Current (VOUT < GND; VOUT > VCC)	lok	+20	mA
DC Output Current, per Pin	lout	+25	mA
DC Supply Current, V _{CC} and GND	Icc	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

^{*} Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	Vcc	4.5	5.5	V
DC Input Voltage	VIN	0.0	5.5	V
DC Output Voltage V _{CC} = 0 High or Low State	Vout	0.0 0.0	5.5 VCC	V
Operating Temperature Range	T _A	- 55	+85	°C
Input Rise and Fall Time $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	t _r , t _f	0 0	100 20	ns/V

[†]Derating — SC-88A Package: -5 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS

			VCC	1	A = 25°0	2	T _A ≤	85°C	T _A ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
VIL	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
VOH	Minimum High–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50\mu\text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	VIN = VIH or VIL	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4\text{mA}$ $I_{OH} = -8\text{mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
VOL	Maximum Low–Level Output Voltage	VIN = VIH or VIL	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	VIN = VIH or VIL	VIN = VIH or VIL IOL = 4mA IOL = 8mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
IN	Maximum Input Leakage Current	V _{IN} = 5.5V or GND	0 to 5.5			±0.1		±1.0		±1.0	μА
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μА
ГССТ	Quiescent Supply Current	Per Input: V _{IN} = 3.4V Other Input: V _{CC} or GND	5.5			1.35		1.50		1.65	mA
lopd	Output Leakage Current	V _{OUT} = 5.5V	0.0			0.5		5.0		10	μΑ

AC ELECTRICAL CHARACTERISTICS (Cload = 50 pF, Input t_{Γ} = t_f = 3.0ns)

			1	A = 25°	2	T _A ≤	85°C	T _A ≤ '	125°C		
Symbol	Parameter	Test Condi	Test Conditions		Тур	Max	Min	Max	Min	Max	Unit
^t PLH [,] ^t PHL	Maximum Propogation Delay,	$V_{CC} = 3.0 \pm 0.3 V$	$C_L = 15 pF$ $C_L = 50 pF$		4.5 5.8	10.0 13.5		11.0 15.0		13.0 17.5	ns
	Input A or B to Y	$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15 pF$ $C_L = 50 pF$		3.0 3.8	6.7 7.7		7.5 8.5		8.5 9.5	
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0V	
PD	Power Dissipation Capacitance (Note 1.)	11	pF

^{1.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in}+I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in}+I_{CC} • V_{CC}.

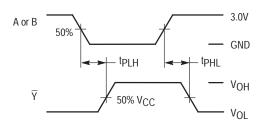
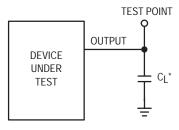


Figure 2. Switching Waveforms



*Includes all probe and jig capacitance

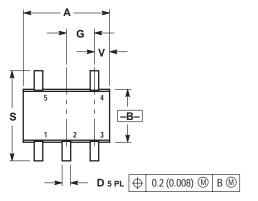
Figure 3. Test Circuit

DEVICE ORDERING INFORMATION

Device Order Number	Circuit Indicator	Temp Range Identifier	Tech- nology	Input Type	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1GT02DFT1	MC	74	VHC1G	Т	02	DF	T1	SC-88A/ SOT-353	7–Inch/3000 Unit

PACKAGE DIMENSIONS

SC-88A / SOT-353 **DF SUFFIX** 5-LEAD PACKAGE CASE 419A-01 ISSUE B

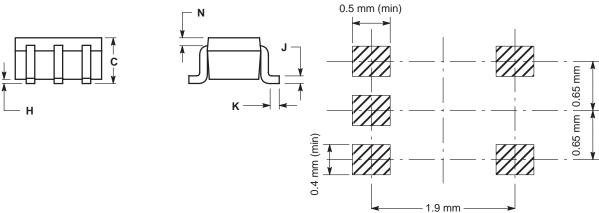


- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	REF	0.20	REF
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40



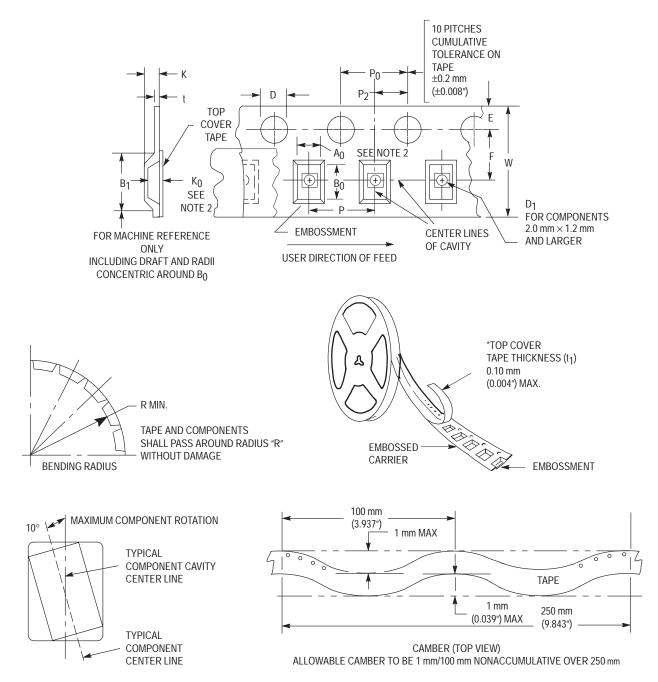


Figure 4. Carrier Tape Specifications

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Tape Size	B ₁ Max	D	D ₁	E	F	К	Р	P ₀	P ₂	R	Т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

Metric Dimensions Govern–English are in parentheses for reference only.
 A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

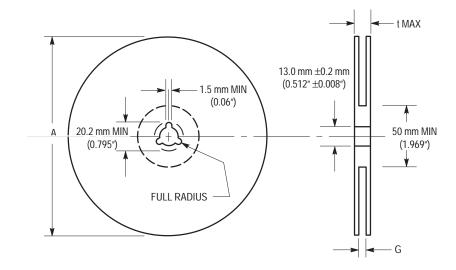


Figure 5. Reel Dimensions

REEL DIMENSIONS

Tape Size	A Max	G	t Max
8 mm	330 mm	8.400 mm, +1.5 mm, -0.0	14.4 mm
	(13")	(0.33", +0.059", -0.00)	(0.56")

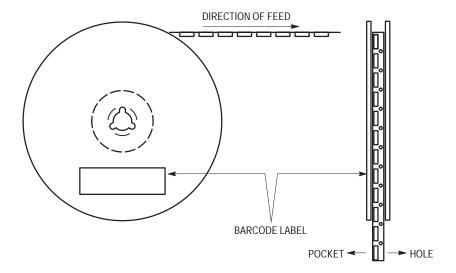


Figure 6. Reel Winding Direction

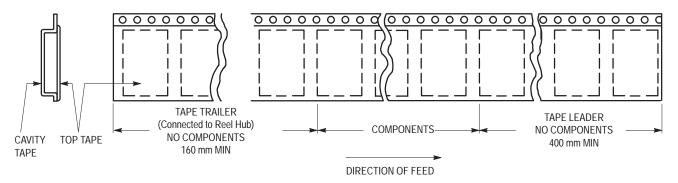


Figure 7. Tape Ends for Finished Goods

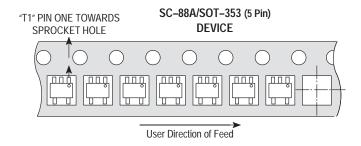


Figure 8. Reel Configuration

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